

FORM PTO-1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY.DOCKET NO. 06293P2 USA	SERIAL NO.
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		APPLICANT Peng Zhang, et al.	
		FILING DATE	GROUP
(37 CFR 1.98(b))			

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION		
		YES	NO												
EP	1	1	1	5	0	3	5			Europe				X	
JP	95	1	4	2	3	4	9			Japan				X	
JP	96	0	0	8	1	6	3			Japan				X	
WO	0	0	0	3	3	0	6			World				X	
WO	0	2	2	3	5	9	8			World				X	
WO	8	7	0	3	3	8	7			World				X	
WO	9	9	1	5	6	0	9			World				X	
WO	9	9	6	0	0	8	3			World				X	
WO	9	9	6	0	4	4	8			World				X	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		Domke, W. D., et al., "Pattern Collapse in High Aspect Ratio DUV and 193nm Resists," Proc. SPIE-Int. Soc. Opt. Eng. 3999, 313-321, 2000.
		Cheung, C., et al., "A Study of a Single Closed Contact for 0.18 Micron Photolithography Process," Proc. SPIE-Int. Soc. Opt. Eng. 3998, 738-741, 2000.
		S. Hien, et al., "Collapse behavior of single layer 193 and 157 nm resists: Use of surfactants in the rinse to realize the sub 130 nm nodes," Infineon Technologies, International SEMATECH, Center for Nano Technology, University of Wisconsin.
		T. Tanaka, et al., "Mechanism of Resist Pattern Collapse During Development Process," Jpn. J. Appl. Phys. Vol. 32 (1993), pp. 6059-6064, Part 1, No. 12B.

EXAMINER _____ **DATE CONSIDERED** _____

EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.